

High-performance GaN-based HEMTs

The PhD candidate will work on the design, modelling, and fabrication of high-performance GaN-based High Electron Mobility Transistors (HEMTs) including:

- Development of nanoscale devices by E-Beam Lithography (EBL) and Thermal Scanning Probe Lithography (t-SPL) in normally-on and normally-off HEMT structures
- Exploration of the integration of 2D materials for enhanced HEMT performance

The research will be conducted at the Institute for Optoelectronic Systems and Microtechnology (www.isom.upm.es), Technical University of Madrid. The candidate will pursue an industrial PhD in a joint program with INDRA Sistemas S. A., a Spanish multinational company, within the project “Chair UPM-INDRA in Microelectronics”

WHAT WE OFFER

- Three-year contract. Annual gross salary of 25,350 € and health and social benefits according to Spanish law
- Excellent facilities, international atmosphere, and partnering with industry

WHAT WE NEED

- A Master degree in Electronic/Telecommunication/Materials Engineering or Physics
- Proficiency in English, goal-oriented mindset, creativity, teamwork & communication skills. Previous research experience will be highly valued
- Applicants should send a motivation letter & CV to Jorge Pedrós (j.pedros@upm.es)

